

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5458

SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS

DC-DC CONVERTER APPLICATIONS

DC-AC INVERTER APPLICATIONS

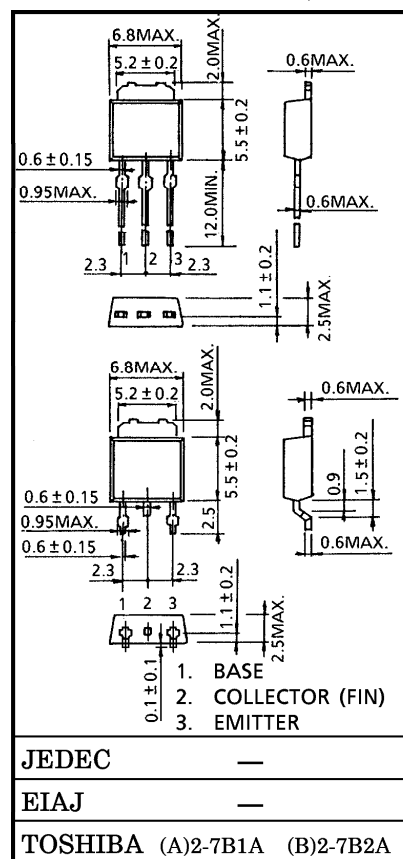
INDUSTRIAL APPLICATIONS

Unit in mm

- Excellent Switching Times
: $t_r = 0.7 \mu s$ (Max.), $t_f = 0.5 \mu s$ (Max.) ($I_C = 0.3 A$)
- High Collector Breakdown Voltage : $V_{CEO} = 400 V$

MAXIMUM RATINGS ($T_a = 25^\circ C$)

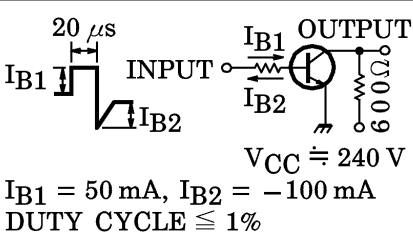
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	600	V
Collector-Emitter Voltage		V_{CEO}	400	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	0.8	A
	Pulse	I_{CP}	1.5	
Base Current		I_B	0.5	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	1.0	W
	$T_c = 25^\circ C$		10	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$



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ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 480\text{ V}, I_E = 0$	—	—	100	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	100	μA
Collector-Base Breakdown Voltage		$V_{(BR) CBO}$	$I_C = 1\text{ mA}, I_E = 0$	600	—	—	V
Collector-Emitter Breakdown Voltage		$V_{(BR) CEO}$	$I_C = 10\text{ mA}, I_B = 0$	400	—	—	V
DC Current Gain		h_{FE}	$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$	12	—	—	
			$V_{CE} = 5\text{ V}, I_C = 0.08\text{ A}$	20	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C = 0.3\text{ A}, I_B = 0.04\text{ A}$	—	—	1.0	V
	Base-Emitter	$V_{BE(sat)}$	$I_C = 0.3\text{ A}, I_B = 0.04\text{ A}$	—	—	1.3	
Switching Time	Turn-on Time	t_r	 $20\ \mu\text{s}$ I_{B1} INPUT I_{B2} $V_{CC} \doteq 240\text{ V}$ $I_{B1} = 50\text{ mA}, I_{B2} = -100\text{ mA}$ $\text{DUTY CYCLE} \leq 1\%$	—	—	0.5	μs
	Storage Time	t_{stg}		—	—	2.0	
	Fall Time	t_f		—	—	0.3	

